

WHAT IS CLAIMED IS

1. A plasma etching apparatus comprising:  
5        a lower electrode supporting a semiconductor substrate;  
a focus ring disposed along a circumference of said  
semiconductor substrate;  
a sensor for measuring a position of an upper surface of said  
focus ring;  
a drive mechanism for driving said focus ring vertically; and  
10      a controller for adjusting the position of the upper surface  
of said focus ring by driving said drive mechanism on the basis of  
a result of measurement by said sensor.

15      2. The plasma etching apparatus according to claim 1,  
wherein said sensor can measure the position of the upper  
surface of said focus ring at a plurality of points of said focus  
ring, and  
20      said drive mechanism can change the position of the upper  
surface of said focus ring at a plurality of points of said focus  
ring.

25      3. A plasma etching method comprising:  
a measurement step of measuring an upper surface of a focus  
ring;  
an adjustment step of adjusting a position of the upper surface  
of the focus ring by driving the focus ring vertically on the basis  
of the result of measurement by said measurement step; and  
30      an etching step of performing etching after finishing said  
adjustment step.

35      4. The plasma etching method according to claim 3,

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wherein said measurement step includes a step of measuring the upper surface of the focus ring at a plurality of points of the focus ring, and

5 said adjustment step includes a step of adjusting the position of the upper surface of the focus ring at a plurality of points of the focus ring on the basis of the result of measurement by said measurement step.